E ect of kink-rounding barriers on step edge uctuations

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A bstract

The e ect that an additional energy barrier E $_{\rm kr}$ for step adatom s m oving around kinks has on equilibrium step edge uctuations is explored using scaling arguments and kinetic M onte C arbo simulations. When m ass transport is through step edge di usion, the time correlation function of the step uctuations behaves as C (t) = A (T)t^{1=4}. At low temperatures the prefactor A (T) shows A rrhenius behavior with an activation energy (E $_{\rm det}$ + 3)=4 if E $_{\rm kr}$ < and (E $_{\rm det}$ + E $_{\rm kr}$ + 2)=4 if E $_{\rm kr}$ > , where is the kink energy and E $_{\rm det}$ is the barrier for detachment of a step adatom from a kink. We point out that the assumption of an E instein relation for step edge di usion has lead to an incorrect interpretation of step uctuation experiments, and explain why such a relation does not hold. The theory is applied to experimental results on Pt(111) and Cu (100).

K ey words: M odels of surface kinetics, A tom istic dynam ics, Surface di usion, Stepped single crystal surfaces, M onte C arlo simulations

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1 Introduction

In thin Im growth the detailed know ledge of the microscopic elementary processes is essential since the large scale morphology is determined by the competition between the nonequilibrium deposition ux and the dierent relaxation mechanisms [1]. Clear demonstrations of this are for example growth instabilities on high symmetry or vicinal crystal surfaces, which are known to produce self-organized nanoscale patterns [2,3]. In both cases, mound formation on singular [4] and step meandering on vicinal surfaces [5], the size of the structures is set by the relation between the time scales of deposition and relaxation kinetics [6]. Thus the knowledge of the relaxation kinetics opens a possibility to control the size of the structures by controlling the external parameters such as deposition rate and temperature.

The most important elementary process on surfaces is the hopping of individual atoms. The motion of an adatom from one lattice site to another is a thermally activated process and takes place at rate

$$_{i} = _{i;0} \exp \left(\quad E_{i} \right); \tag{1}$$

where = $1=k_B$ T is the inverse tem perature, $_{i;0}$ is an attempt frequency, and E $_i$ is the activation energy of the process i. Thus know ledge of the activation energies gives access to the elementary rates. Unfortunately the activation energies are very rarely accessible by direct measurement; it is extremely discult to follow a single atom disusing on a surface and to extract activation energies from its trajectory. Thus one has to rely on measurements of mesoscopic quantities and try to compare these with theoretical predictions in order to extract the microscopic parameters. Examples of such an approach are the determination of the adatom disusion barrier from the island density [7], the estimate of interlayer disusion barriers from second layer nucleation experiments and mound shapes [8,9], and the extraction of activation energies for processes at step edges from the characteristic length scales of growth instabilities on vicinal surfaces [10{12}].

An elegant method for measuring energetic and kinetic parameters of atom istic processes at steps exploits the time correlation function of equilibrium step uctuations, see [13,14] for recent reviews. In this paper we revisit the theoretical basis of these experiments for the case of mass transport dominated by step edge di usion, and take into account the possibility of a significant kink rounding barrier, which prevents adatom s m igrating along a step from hopping around a kink. The kink-rounding barrier is the one-dimensional analog of the well-known Ehrlich-Schwoebel (ES) barrier [15] suppressing the inter-layer mass transport on crystal surfaces. It is worth noting that also a three-dim ensional analog of the ES barrier, inhibiting atom s going around facet edges, has been observed [16]. The existence of the kink rounding barrier is still under debate; num erical calculations support its existence [17,18], but until now experim ental observations are few [19,20]. If present, the kinkrounding barriers have great im pact on the patterns form ed under unstable epitaxial growth [11,21{25}] as well as on the shape relaxation of islands and other nanostructures [26,27]. In this paper we show how kink-rounding barriers a ect equilibrium step uctuations, thus providing an alternative way of determ in ing the barriers experimentally. In addition, in Sect. 4 we clarify a m isconception in the theory of step uctuations which has lead to an incorrect data analysis in some cases.

2 Step uctuations and the adatom m obility

On a vicinal surface the mono-atom ic steps, separating high symmetry terraces, are not perfectly straight but wander due to thermal uctuations. Here we will consider a situation where adatoms cannot detach from the steps, thus the only possible mass transfer process is migration of adatoms along the steps. The Langevin theory of step uctuations then yields the expression [13,14]

C (t) h[(x;t)
$$(x;0)^2$$
]i = $a_1^2 \frac{(3=4)}{(2-1)^{1=2}}$ (2 ~t) 1=4 (2)

for the time correlation function of the step edge position (x;t) with the initial condition of a at step, (x;0) 0. Here ~ is the step stimess, a the lattice spacing perpendicular to the step, is the atom ic area, (3=4) 1:2254:::, and denotes the adatom mobility along the step edge. It is dened through the relation

$$\dot{j} = \theta_x = \theta_x - \theta_{xx}$$
 (3)

between the mass current along the step and the chemical potential gradient driving it. In the last equality the G ibbs-Thom son relation has been used.

To make use of the expression (2) for the analysis of experimental data, the parameters ~ and of the continuum description must be expressed in terms of the rates of the elementary processes. This can be done exactly if the step is modeled as a one-dimensional solid-on-solid (SOS) surface with energy barriers proportional to the number of lateral bonds in the initial state (Arrhenius kinetics); see Sect.3 for a precise de nition. In this case one obtains [28]

$$= \frac{a_0}{2} \exp \left(E_{det} \right) \tag{4}$$

and

$$\sim = a^{-1} (\cosh () 1);$$
 (5)

where $E_{\rm det}$ denotes the energy barrier for detachment of a step atom from a kink site, the kink energy—is the energy cost of creating a kink, a is the lattice constant parallel to the step, and $_0$ is the attempt frequency, which is assumed to be the same for all processes. Since the detachment of a kink atom creates two kinks, within the Arrhenius model $E_{\rm det} = E_{\rm st} + 2$, where $E_{\rm st}$ is the energy barrier for disusion along the straight (unkinked) step. Figure 1 shows

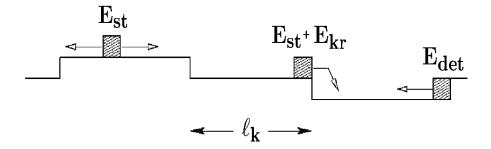


Fig. 1. A schematic picture of a monoatom ic step with the activation energies of the elementary processes.

a cartoon of a step displaying the relevant processes. The relation $e^{E_{det}}$ has also been derived within a Kubo form alism [29,30].

Putting everything together yields

C (t)=
$$a_2^2 = g$$
 $\frac{t}{st}$ (6)

where g is a num errical constant of order unity, and st 3 = is the characteristic time for the step to uctuate one lattice constant. In the low temperature limit 1 one nds

$$_{\rm st}$$
 exp [(E_{det} + 3)]: (7)

Equations (6) and (7) form the basis of the experimental determination of kinetic barriers from step edge—uctuations. Measuring the coe-cient of the t^{1-4} -behavior of the correlation function (6), the activation energy of the characteristic time (7) can be obtained. Provided the kink energy—is known from other sources (e.g., from the analysis of static step—uctuations [13,14]), this yields an estimate of the detachment barrier $E_{\rm det}$.

To see how (7) has to be modilled in the presence of kink rounding barriers, we list rederive st from a scaling argument. The elementary process driving the step luctuations is the transport of an atom from one kink to another, which allows the kinks to diluse along the step. In order to move the step by a distance a_2 , a kink must diluse over a distance of the order of the mean kink spacing k = (1-2)ae. The detachment rate of atoms from a kink site is k = 0 exp (k = 0). The probability k = 0 at for an emitted adatom to reach another kink at distance k = 0 before it reattaches to the original kink can be calculated

from a random walk theory [31], yielding $P_{att} = \frac{1}{k}$. Thus the discussion rate of a kink is $_{det}P_{att}$ and the characteristic time for a step to suctuate over a single lattice constant reads $_{st} = \frac{2}{k} = (_{det}P_{att}) = \exp{[(3 + E_{det})]}$, in agreement with (7).

When atoms discussing along the step experience an extra barrier E_{kr} for going around a kink site, as drawn in Fig.1, the probability P_{att} of the adatom to attach to a kink at distance k is altered. A fter reaching the distant kink the adatom still has to overcome the kink rounding barrier in order to attach to it. This yields [31]

$$P_{att.} = (k + 1 = p_{kr})^{-1};$$
 (8)

where $p_{kr}=\exp\left(-E_{kr}\right)$ is the probability for going around a kink. Com paring k_k with p_{kr}^{-1} it is obvious that the kink rounding barriers are relevant if $k_{kr}>$. In this case (7) has to be replaced by

st
$$\exp [(2 + E_{det} + E_{kr})]$$
: (9)

As shown before the characteristic time is generally a combination of the adatom mobility and the step sti ness, st $^3=$. Since the step sti ness does not depend on the dynamics of the adatom s along the step, but only on the energetics, we may conclude that the adatom mobility is reduced to

$$\exp\left(\left(\mathbb{E}_{det} + \mathbb{E}_{kr}\right)\right) \tag{10}$$

by the kink-rounding barrier, when E $_{\rm kr}$ > $\,$. The expression (8) suggests the interpolation formula

$$= \frac{1}{2} a_{0} \frac{e^{\frac{E_{det}}{1 + e^{\frac{(E_{kr})}{1}}}}}{1 + e^{\frac{(E_{kr})}{1}}}$$
 (11)

for the m obility, which recovers (4) for E_{kr}

3 M onte Carlo simulations

In order to con $\,$ m the validity of the arguments of the previous section we have conducted M onte Carlo $\,$ simulations of a $\,$ simple one-dimensional SOS m odel. The position of the step at site i is h_i and the atom $\,$ s $\,$ m ay hop along the step to neighboring sites (i! i 1) with rate

$$_{i;i} _{1} = _{0} \exp (E_{i;i} _{1})$$
 (12)

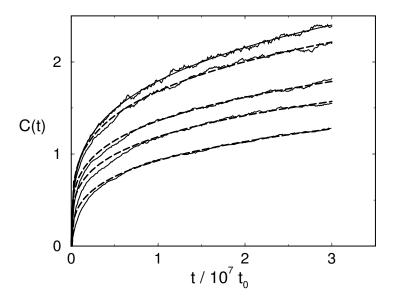


Fig. 2. The time correlation function (Eq. (14)) for = 2.5 and $E_{\rm kr}=0.0=0.4=1.2=1.6=2.0$ (from top to bottom). The dashed line is the best $t\,A\,t^{1=4}+B$. Time is measured in units of the inverse di usion rate along at a step, $t_0=1=(0.0)$ 0 exp[$E_{\rm st}$])

where the activation energy depends on the local con guration as

$$E_{i;i-1} = E_{st} + 2 n_i + [1 (h_i h_{i-1} 1)] E_{kr}$$
: (13)

Here $n_i=0$;1;2 is the number of lateral nearest neighbors of the atom at initial site i and E_{kr} is an extra barrier suppressing kink rounding; whenever the hop from i! i 1 is not along at step i.e. h h_{i-1} 6 1, the extra barrier E_{kr} is added. In the simulations we used a lattice of size L=131072, starting with a straight step h_i (0) 0.

The hopping rate $_0\exp[$ E $_{\rm st}]$ of a free step edge atom on an unkinked step segment determines the time scale of the model, and can be set to unity in the simulation. For the kink energy we used the value = 0.1 eV. The kink-rounding barrier E $_{\rm kr}$ was varied between 0 and 0.24 eV, and the inverse temperature in the interval = 1.25 3.5, corresponding to T = 331 928 K.

The time-correlation function

C (t)
$$h_{i}$$
 (t)² (14)

m easured from the simulations is shown in Fig. 2. It has a clear t^{1-4} time dependence and the prefactor in Eq. (2) was determined by thing the data

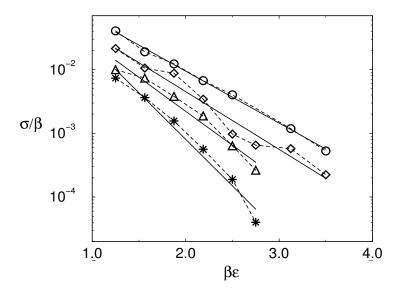


Fig. 3. The adatom mobility along the step edge obtained from the prefactor of the correlation function in Fig. 2, with = 0:1 eV and kink rounding barrier $E_{\rm kr}=$ = 0:0();1:2(3);1:6(4);2:4(). The full lines are best to an Arrhenius form.

in the long time limit with C (t) = $At^{1-4} + B$. Using Eqs.(2) and (5), the mobility can be extracted from the prefactor. The mobility obtained from the simulation results is shown in Fig. 3 and the activation energy for the mobility E , determined from a to the Arrhenius plot, is shown in Fig. 4. There is a cross-over in the behavior of the activation energy E as the kink-rounding barrier roughly equals the kink energy $E_{\rm kr}$. Thus the simulation results are in good agreement with the analytical results (Eqs. (4) and (10)) of the previous section.

4 No Einstein relation for step edge di usion

In the literature [14,32,33] the interpretation of experim ental step uctuation data is often based on an E instein relation $[34\{36]]$

$$= \frac{n_{st}D_{st}}{k_{B}T}$$
 (15)

for the mobility, where $n_{\rm st}$ is the (one-dimensional) concentration of step adatoms and D $_{\rm st}$ denotes the tracer di usion coe cient for an adatom migrating along a kinked step. The latter can be estimated by considering the motion of an adatom in a model potential where kink sites are represented as traps of depth E $_{\rm det}$ spaced at the mean kink distance [32,33]. The resulting activation energy for D $_{\rm st}$ is E $_{\rm det}$. Since a step adatom can be viewed as a

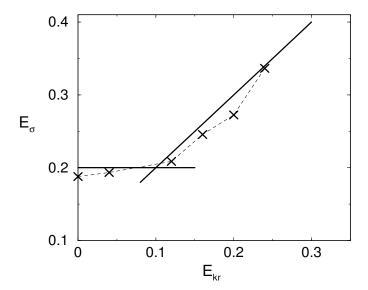


Fig. 4. The activation energy for the adatom mobility obtained from the ts in Fig 3.A clear cross-over in the behavior is seen at $E_{\rm kr}$ = 0:1. The full lines are the theoretical predictions Eqs. (4) and (10).

double kink, the concentration of step adatom s in equilibrium is n_0 e 2 = k_B T , and hence the activation energy of is predicted by (15) to be E $_{\rm det}$ + , in disagreem ent with the exact result (4).

N evertheless a relation of the form (4) does hold, if D $_{\rm st}$ is replaced by the diffusion coe cient (1=2)a 2 $_0$ exp [$E_{\rm st}$] for the m igration along a straight close packed step, and the bond counting relation $E_{\rm det}=E_{\rm st}+2$ is assumed. Then (15) simply expresses the balance between the detachment and attachment of step adatoms at the kinks.

5 Conclusions

We have studied the time uctuations of a monoatom ic step when the mass transport is restricted to migration along the step. The scaling arguments presented in this paper Eqs. (9) and (10)], show how the adatom mobility along the step is reduced if the kink-rounding hops are suppressed with an extra barrier. The results of our Monte-Carlo simulations con me the validity of the scaling arguments.

T im e-dependent step uctuations open a possibility for the experim entalm easurem ent of the activation energies of elementary processes on a stepped surface [13,14]. The results presented here show that kink-rounding barriers have to be taken into account in the analysis of such experiments. Provided the kink energy is known, the temperature dependence of the prefactor of the time correlation function C (t) gives access to the activation energy E of the adatom mobility. In general, Eqs.(4) and (10) show that E is an upper bound on the detachment barrier E det. For example, the interpretation of the results presented in [33] in the light of our work shows that E det 1.50 0.16 eV for close-packed steps on Pt (111).

When additional inform ation on the energy barriers is available, the analysis of time uctuations may be used to determ ine the strength of the kink-rounding barrier itself. For the close-packed [110]-step on Cu (100), the re-interpretation of the experimental results of [32] for the time uctuations, supplemented with a result of [10] for the disusion barrier $E_{\rm st}$ at a straight step, yields the estimate $E_{\rm kr}$ 0:41 eV [11].

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